TENT AND TRADEMARK OFFICE

ent Application of Steve Hill

10/761,408 (Unofficial) Serial No.

Group Art Unit:

Filed: January 22,2004

Examiner:

For:

LIGHT EMITTING DIODES AND PLANAR OPTICAL LASERS USING IV

SEMICONDUCTOR NANOCRYSTALS

INFORMATION DISCLOSURE STATEMENT

This Information Disclosure Statement is being filed in the manner prescribed by 37 CFR 1.97(b)

- (d) to satisfy the duty under 37 CFR 1.56 to disclose to the Office information, known to

individuals associated with the filing and prosecution of the subject application, which is

material to the examination of the application.

In accordance with 37 CFR 1.97(g) and (h), this statement is not to be construed as a

representation that a search has been made or an admission that the information cited herein is, or

is considered to be, material to patentability as defined in 37 CFR 1.56(b).

This information disclosure statement is being filed within three months of the filing date of a

national application, within three months of the date of entry of the national stage as set forth in

37 CFR 1.491 in an international application; or before the mailing date of a first official action

on the merits and therefore applicant respectfully requests consideration under 37 CFR 1.97(b).

In compliance with 37 CFR 1.98(a)(1), a list of all patents, publications or other information

submitted for consideration by the Office is hereby provided by way of the attached Form PTO

1449.

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In compliance with 37 CFR 1.98(a)(2), also enclosed is a legible copy of:

i) each United States and foreign patent;

ii) each publication or that portion which caused it to be listed; and

iii) all other information or that portion which caused it to be listed, excluding any

copies of a United States patent application.

It is respectfully requested that the information be expressly considered by the Examiner and that

the references be made of record and appear among the "References Cited" on any patent to issue

therefrom.

The Patent Office is hereby authorized to charge any deficiency, or credit any overpayment in

fees to Deposit Account Number 19-2550.

Respectfully submitted,

STEVEN E. HIL

Dated: April 21, 2004

Ralph A. Dowell

Reg. No. 26,868

Encls.:

Form PTO-1449

All references listed on Form PTO-1449

Acknowledgement Card

| Form PTO-1449 (Modified) | JOHE? | Atty. Docket No. 50422-6 | Serial No. 10/761,408 | |
|--|--------------|------------------------------|-----------------------|--|
| LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION | AUG 1 6 2004 | Applicant Steven E. Hill | | |
| DISCLOSURE STATEMENT (Use several sheets if necessary) | EFFE MAN | Filing Date January 22, 2004 | Group | |
| REFERENCE DESIGNATION U.S. PATENT DOCUMENTS | | | | |

U.S. PATENT DOCUMENTS SUB EXAM. FIL.DATE IF **CLASS DOCUMENT NUMBER** DATE **NAME CLASS APPROPRIATE** INIT. 372 43 8 8 Jul 18, 1995 Lawandy AA 99 4 4 438 AB 6 2 9 0 1 Sept 25, 2001 Jacobson et al.

200 AC 0 1 7 6 5 7 Feb 14, 202 Coffa et al. 257 0 0 7 0 2 1 Jun 13, 2002 Nayfch et al. 205 549 0 1 AD 257 200 0 7 4 6 5 Jun 20, 2002 Flagan et al. ΑE 0 5 79 0 3 Nov 7, 2002 Dal Negro et al. 257 AF 0 1 6 3 0

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EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| Form PTO-1449 (Modified) | OIPA | Atty. Docket No. 50422-6 | Serial No. 10/761,408 |
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| LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION | / % | Applicant Steven E. Hill | - |
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